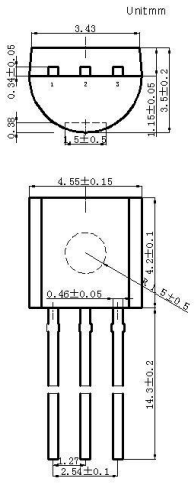
HUIZHOU JINSANE ELECTRONICS CO., LTD

TO-92 Plastic-Encapsulate Transistors



1 . EMITTER

2. BASE

3. COLLECTOR

S8550D TRANSISTOR(PNP)

FEATURE

Excellent h_{FE} Linearity

MAXIMUM RATINGS(Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current	-800	mA
P_C	Collector Power Dissipation	625	mW
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～150	℃

ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100uA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_C=-100uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V，I_C=0			-0.1	μA
DC current gain	$H_{FE(1)}$	V_{CE}=-1.0V，I_C=-50mA	100		400	
	$H_{FE(2)}$	V_{CE}=-1.0V，I_C=-500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.6	V
Collector-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA			-1.2	V
Transition frequency	fT	V_{CE}=-6V, I_C=-20mA f=30 MHZ	150			MHZ

Typical Characteristics